



IR30CDR..L SERIES

HIGH POWER RECTIFIER DIODES

- **Junction Size:** 30 mm Diameter
- **V_{RRM} Class:** 400 to 1000 V
- **Passivation Process:** Diffused Junction

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V _{FM} Maximum Forward Voltage	1.25 V	T _J = 25°C, I _F = 1000 A
V _{RRM} Reverse Breakdown Voltage Range	400 to 1000 V	T _J = 150°C, I _{RRM} = 20 mA

Mechanical Characteristics

Nominal Back Metal Composition	Al - Ni - Au
Nominal Front Metal Composition	Nickel plate Molybdenum disc
Chip Dimensions	30 mm diameter (see drawing)
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

IR30CDR..L Series

Bulletin I0308J 11/01

International
IR Rectifier

Ordering Information Table

Device Code						
IR	30	C	D	R	10	L
①	②	③	④	⑤	⑥	⑦

- 1** - International Rectifier device
- 2** - Chip Dimension in Millimeters
- 3** - Device identifier between chip with same diameter
- 4** - Type of Device: D = Standard Recovery Diode
- 5** - Passivation: R = Rubber for all junctions
- 6** - Voltage code: Code x 100 = V_{RRM}
- 7** - Metallization: L = Nickel plate Molybdenum disc (Anode)
Al - Ni - Au (Cathode)

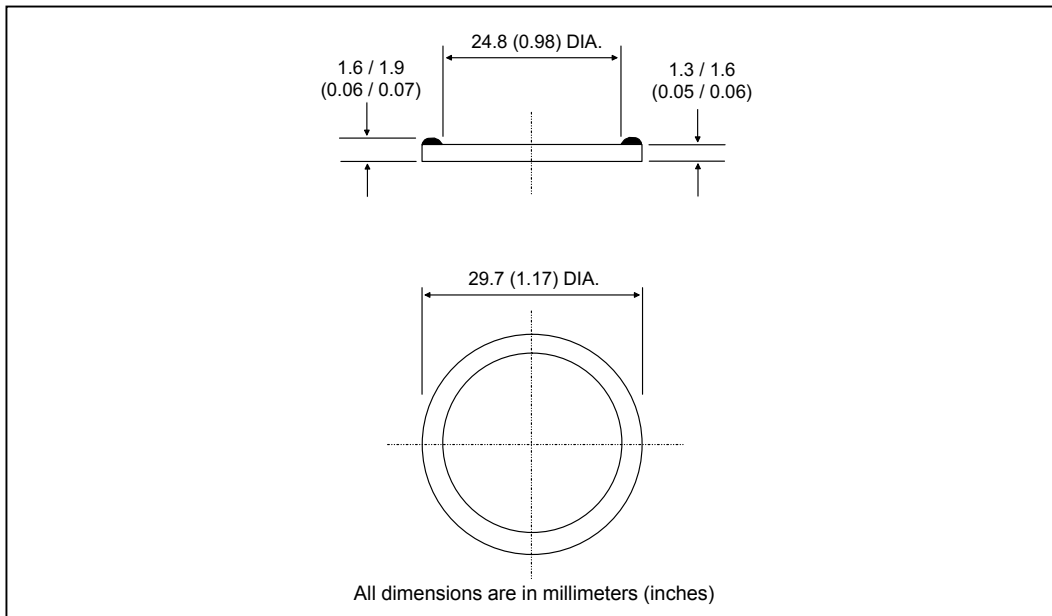
Available Class

04 = 400 V

08 = 800 V

10 = 1000 V

Outline Table



Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

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